

PAPERS in PEER-REVIEWED JOURNALS:

(The numbers in parenthesis next to each publication correspond to the total citations taken on September 2018 from ISI-Web of Science [v.5.30])

55. Observation of standing wave effects in sub-wavelength GaN membranes,

E. Amargianitakis, R. Jayaprakash, F. G. Kalaitzakis, E. Delamadeleine, E. Monroy, N. T. Pelekanos, submitted to Appl. Phys. Lett. December 2018.

54. Spatially Selective Reversible Charge Carrier Density Tuning in WS₂ Monolayers via Photochlorination,

I. Demeridou, I. Paradisanos, C. L. Yuanyue, N. Pliatsikas, P. Patsalas, S. Germanis, N. T. Pelekanos, W. Goddard, G. Kioseoglou, E. Stratakis, accepted in 2D Materials, September 2018.

53. Ultra-low threshold polariton lasing at room temperature in a GaN membrane microcavity with a zero-dimensional trap,

R. Jayaprakash, F. G. Kalaitzakis, G. Christmann, K. Tsagaraki, M. Hocevar, B. Gayral, E. Monroy, N. T. Pelekanos, Scientific Reports 7, 5542 (2017).

52. Highly Uniform Zinc Blende GaAs Nanowires on Si(111) Using a Controlled Chemical Oxide Template,

S. L. Tan, Y. Genuist, E. Bellet-Amalric, M. den Hertog, H. Mariette, N. T. Pelekanos, Nanotechnology 28, 255602 (2017). (1)

51. Room temperature observation of biexcitons in exfoliated WS₂ monolayers,

I. Paradisanos, S. Germanis, N. T. Pelekanos, C. Fotakis, E. Kymakis, G. Kioseoglou, E. Stratakis, Applied Physics Letters 110, 193102 (2017). (9)

50. Enhanced Stark tuning of single InAs (211)B quantum dots due to nonlinear piezoelectric effect in zinc-blende nanostructures,

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48. Structure, Strain and Composition Profiling of InAs/GaAs(211)B Quantum Dot Superlattices

N. Florini, G. P. Dimitrakopoulos, J. Kioseoglou, S. Germanis, C. Katsidis, Z. Hatzopoulos, N. T. Pelekanos, Th. Kehagias, J. of Appl. Phys. 119, 034304 (2016). (4)

47. Assembly of quantum dots on peptide nanostructures and their spectroscopic properties,

Emmanouil Kasotakis, Athanasia Kostopoulou, Miguel Spuch-Calvar, Maria Androulidaki, Nikos Pelekanos, Antonios G. Kanaras, Anna Mitraki, and Alexandros Lappas, Appl. Phys. A-Materials Science & Processing 116, 977-985 (2014). (5)

46. Extraction of absorption coefficients from as-grown GaN nanowires on opaque substrates using all-optical method,

R. Jayaprakash, D. Ajagunna, S. Germanis, M. Androulidaki, K. Tsagaraki, A. Georgakilas, N. T. Pelekanos, Optics Express 22, 19555 (2014). (7)

45. Recombination dynamics in piezoelectric (211)B InAs quantum dots,

S. Germanis, A. Beveratos, C. Gauthron, A. Stavrinidis, G. Konstantinidis, Z. Hatzopoulos, N.T. Pelekanos, Microelectronic Engineering 112, 179 (2013). (2)

44. Residual strain and piezoelectric effects in passivated GaAs/AlGaAs core-shell nanowires,

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43. All dielectric GaN microcavity: Strong coupling and lasing at room temperature,

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- 41. Bragg polariton luminescence from a GaN membrane embedded in all dielectric microcavity,**
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- 40. Piezoelectric InAs (211)B quantum dots grown by molecular beam epitaxy: structural and optical properties,**
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- 38. The effect of annealing on the properties of indium-tin-oxynitride films as ohmic contact for GaN based optoelectronic devices,**
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- 27. Direct comparison of recombination dynamics in cubic and hexagonal GaN/AlN quantum dots,**
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